

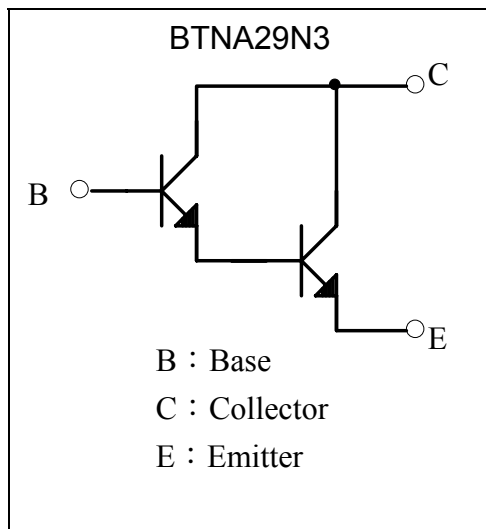
General Purpose NPN Epitaxial Planar Transistor

BTNA29N3

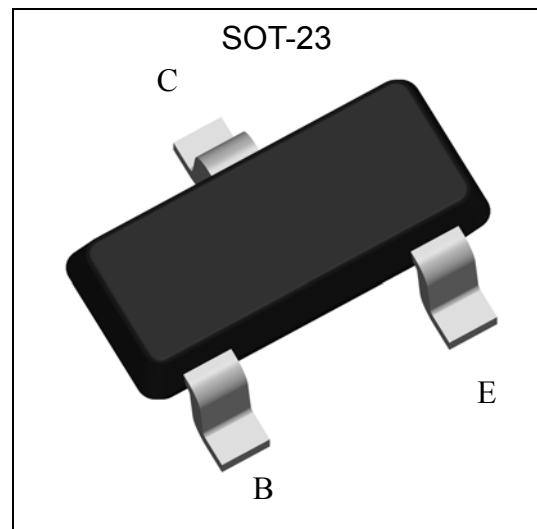
Description

- The BTNA29N3 is a darlington amplifier transistor
- Pb-free lead plating and halogen-free package

Symbol

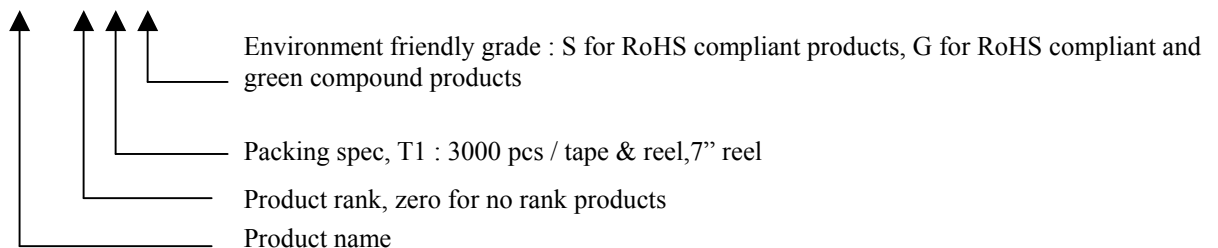


Outline



Ordering Information

Device	Package	Shipping
BTNA29N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CES}	100	V
Emitter-Base Voltage	V _{EBO}	12	V
Collector Current	I _C	0.5	A
Peak Collector Current	I _{CP}	2	A
Power Dissipation	P _D	500 (Note)	mW
Operating Junction Temperature Range	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	190	°C/W
Thermal Resistance, Junction-to-ambient, max (Note)	R _{θJA}	250	

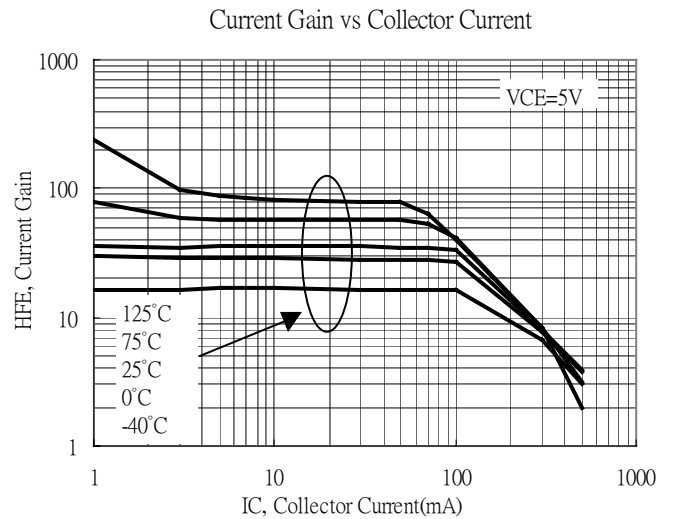
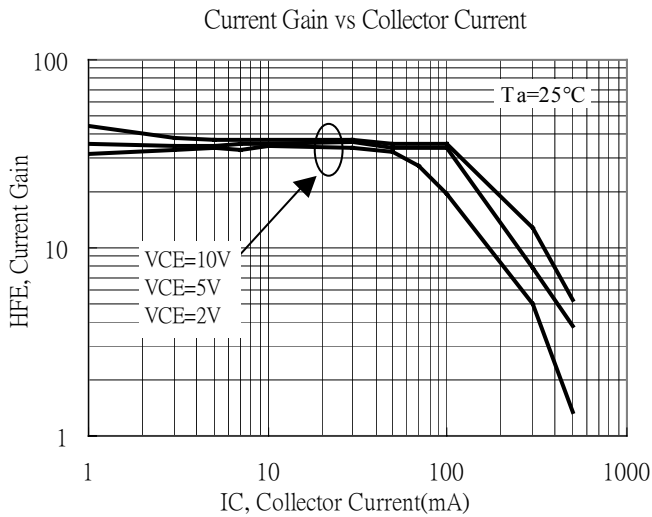
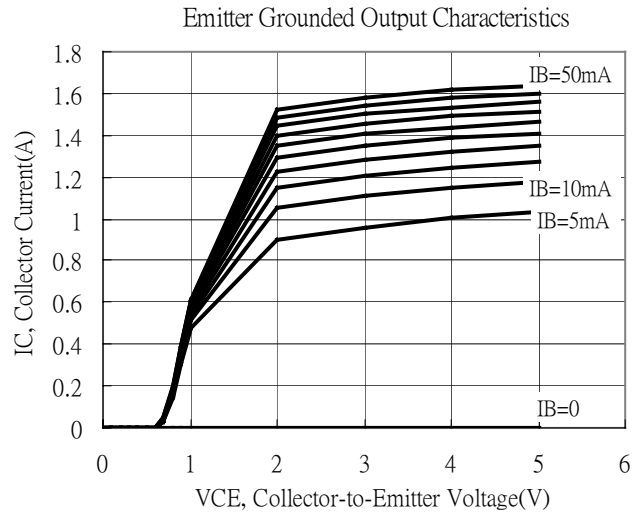
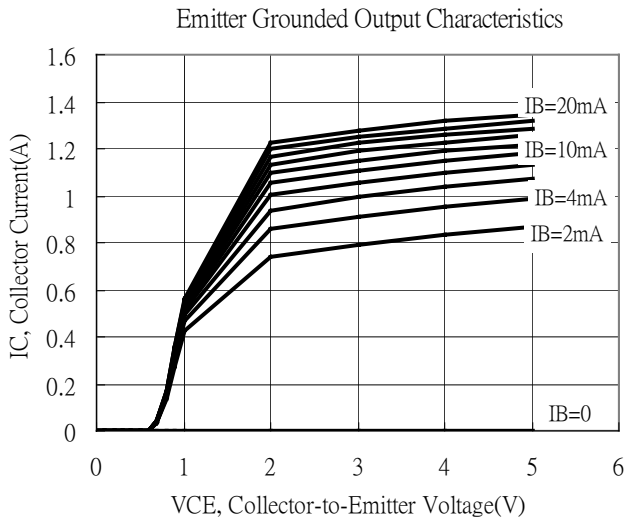
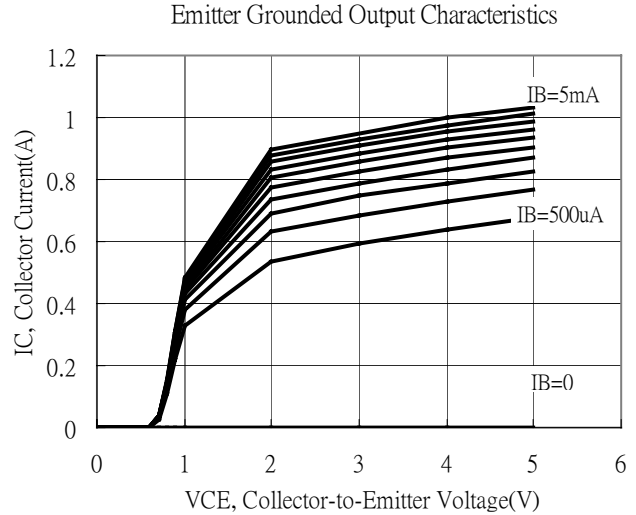
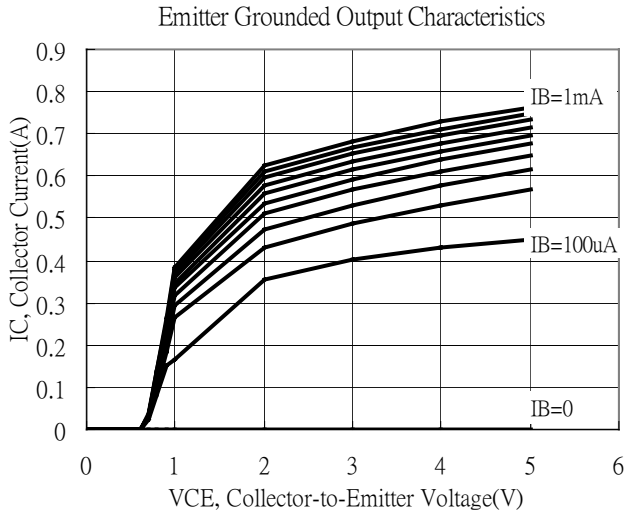
Note : Device is mounted on an FR-4 PCB, single sided, 1oz. copper, tin plated, mounting pad for collector 15mm x15 mm.

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	100	145	-	V	I _C =100μA
BV _{CES}	100	135	-	V	I _C =100μA, V _{BE} =0V
BV _{EBO}	12	18	-	V	I _E =10μA
I _{CB0}	-	-	100	nA	V _{CB} =80V
I _{CES}	-	-	500	nA	V _{CE} =80V
I _{EBO}	-	-	100	nA	V _{EB} =10V
*V _{CE(sat)}	-	0.71	1.0	V	I _C =10mA, I _B =0.01mA
*V _{CE(sat)}	-	0.84	1.1	V	I _C =100mA, I _B =0.1mA
*V _{CE(sat)}	-	-	1.2	V	I _C =500mA, I _B =5mA
*V _{BE(sat)}	-	1.4	1.8	V	I _C =100mA, I _B =0.1mA
*V _{BE(on)}	-	1.35	2.0	V	V _{CE} =5V, I _C =100mA
*h _{FE 1}	10K	-	-		V _{CE} =5V, I _C =10mA
*h _{FE 2}	15K	-	-		V _{CE} =5V, I _C =100mA
*h _{FE 3}	1K	-	-		V _{CE} =5V, I _C =500mA
f _T	125	200	-	MHz	V _{CE} =5V, I _C =10mA, f=100MHz
C _{ob}	-	5	8	pF	V _{CB} =10V, f=100MHz

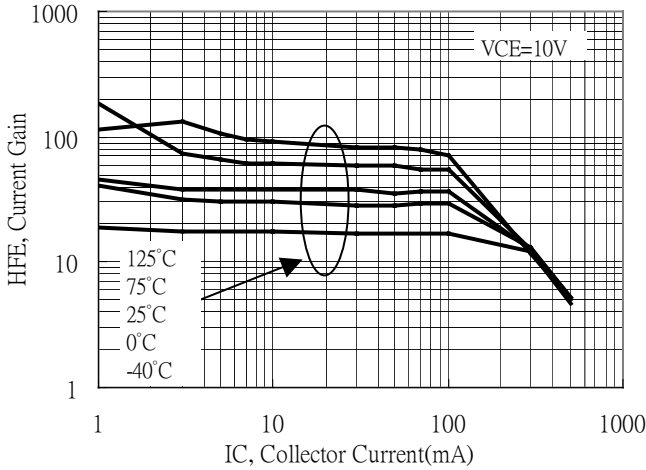
*Pulse Test: Pulse Width ≤300μs, Duty Cycles≤2%

Typical Characteristics

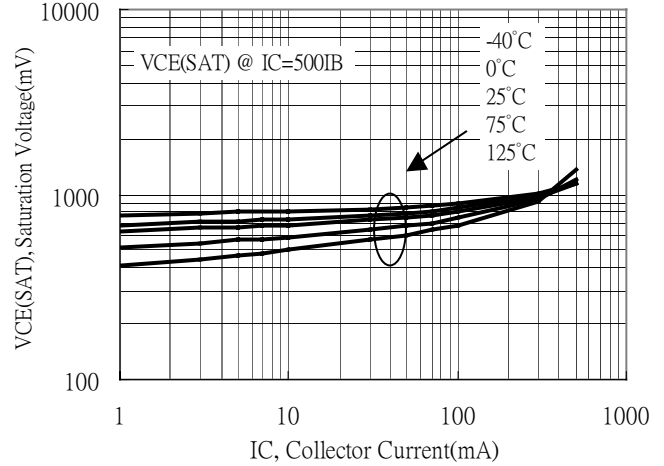


Typical Characteristics(Cont.)

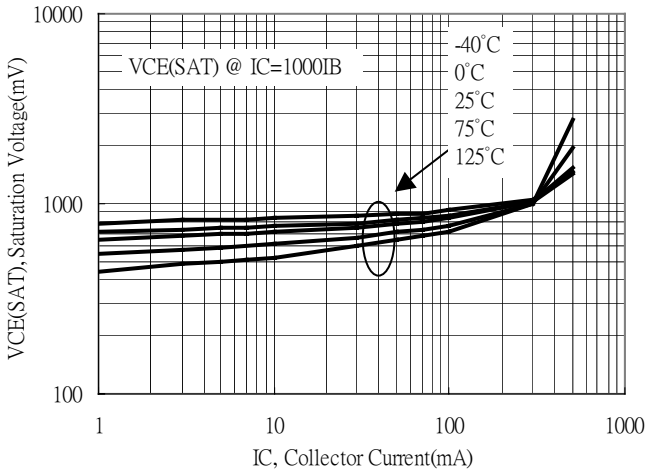
Current Gain vs Collector Current



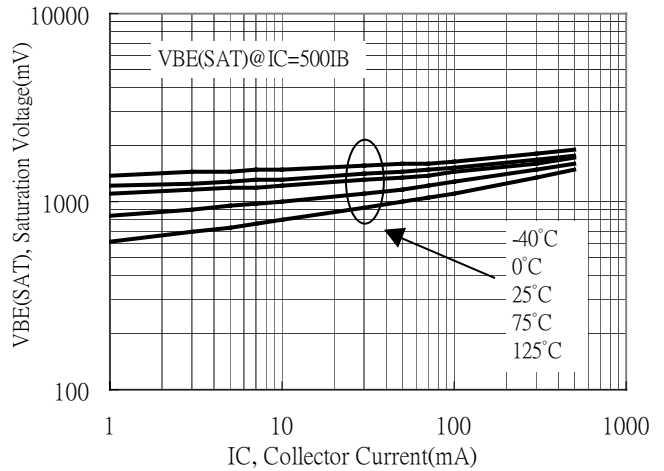
Saturation Voltage vs Collector Current



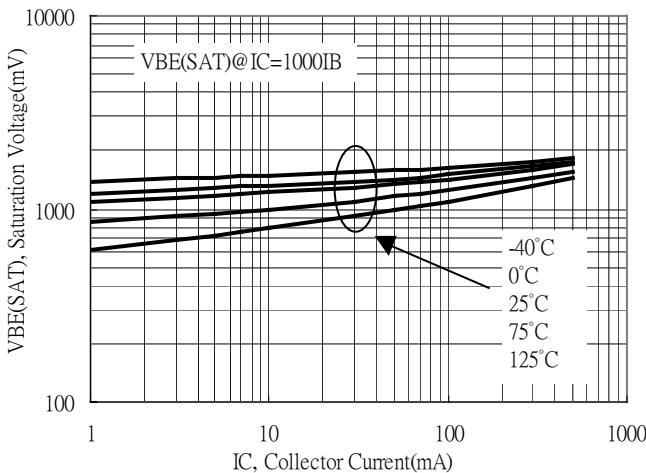
Saturation Voltage vs Collector Current



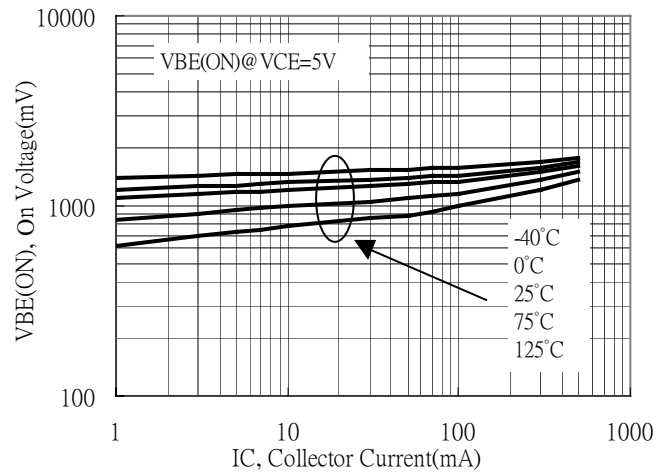
Saturation Voltage vs Collector Current



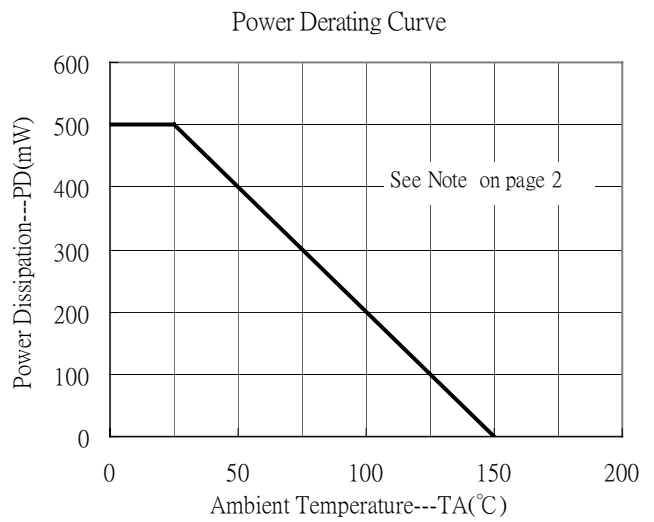
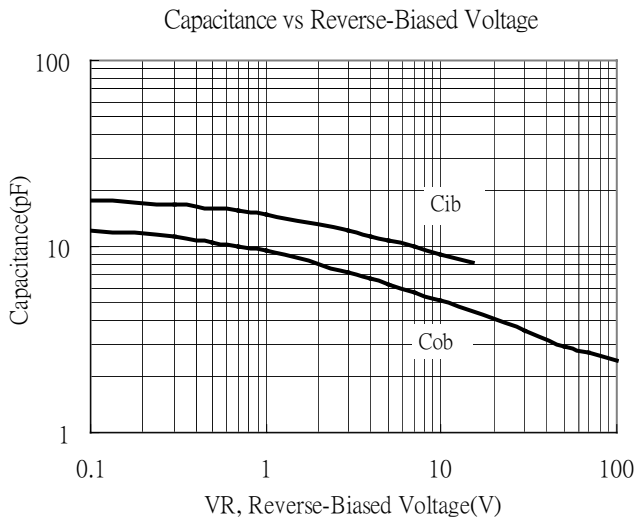
Saturation Voltage vs Collector Current



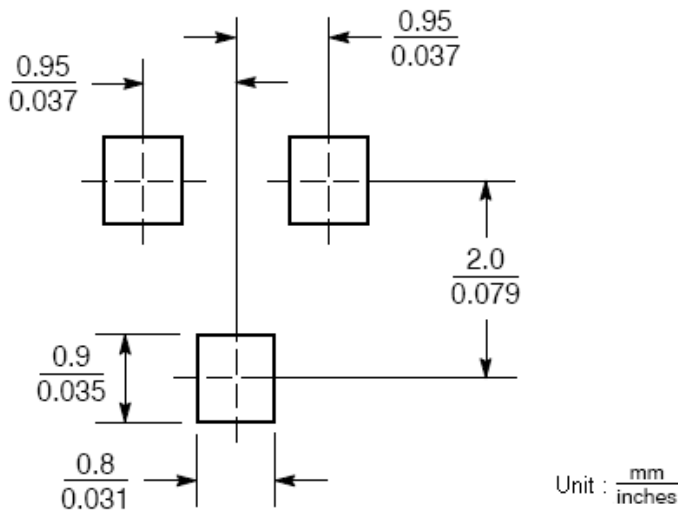
Saturation Voltage vs Collector Current



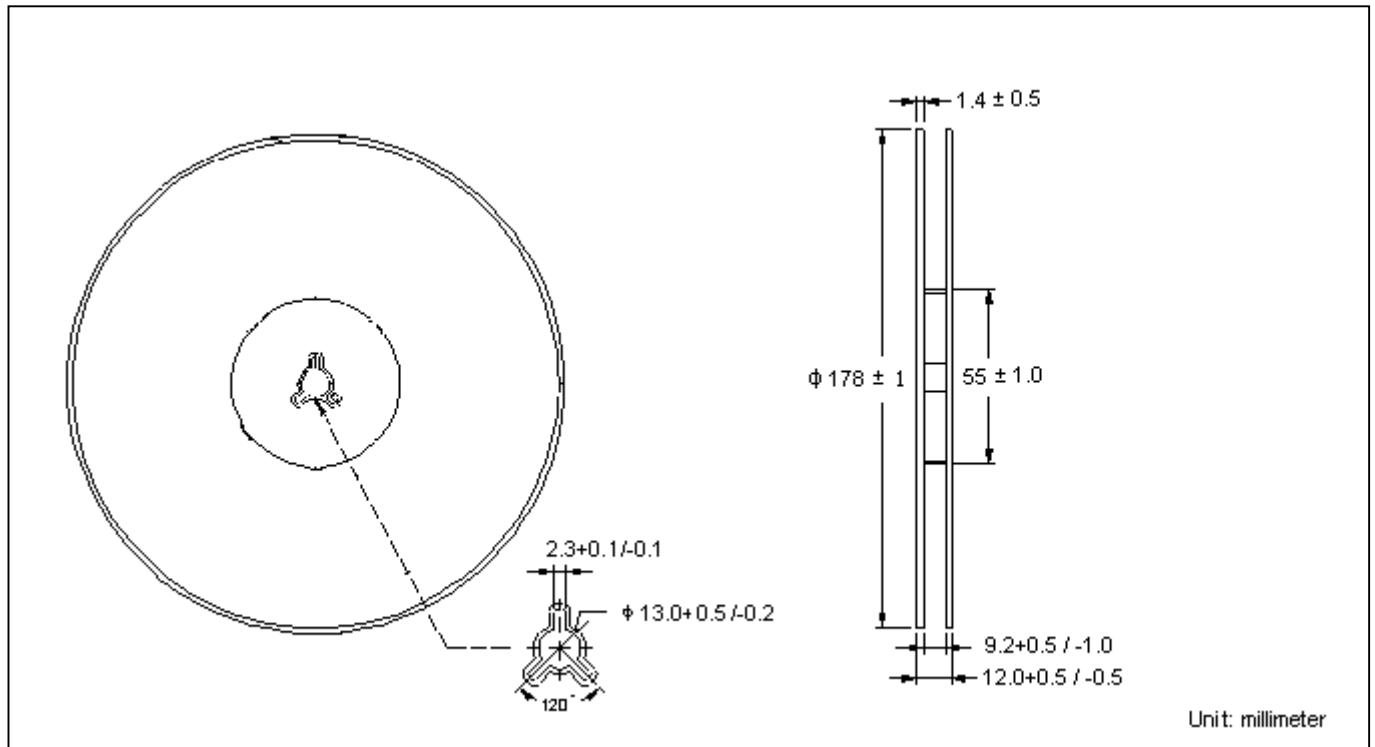
Typical Characteristics(Cont.)



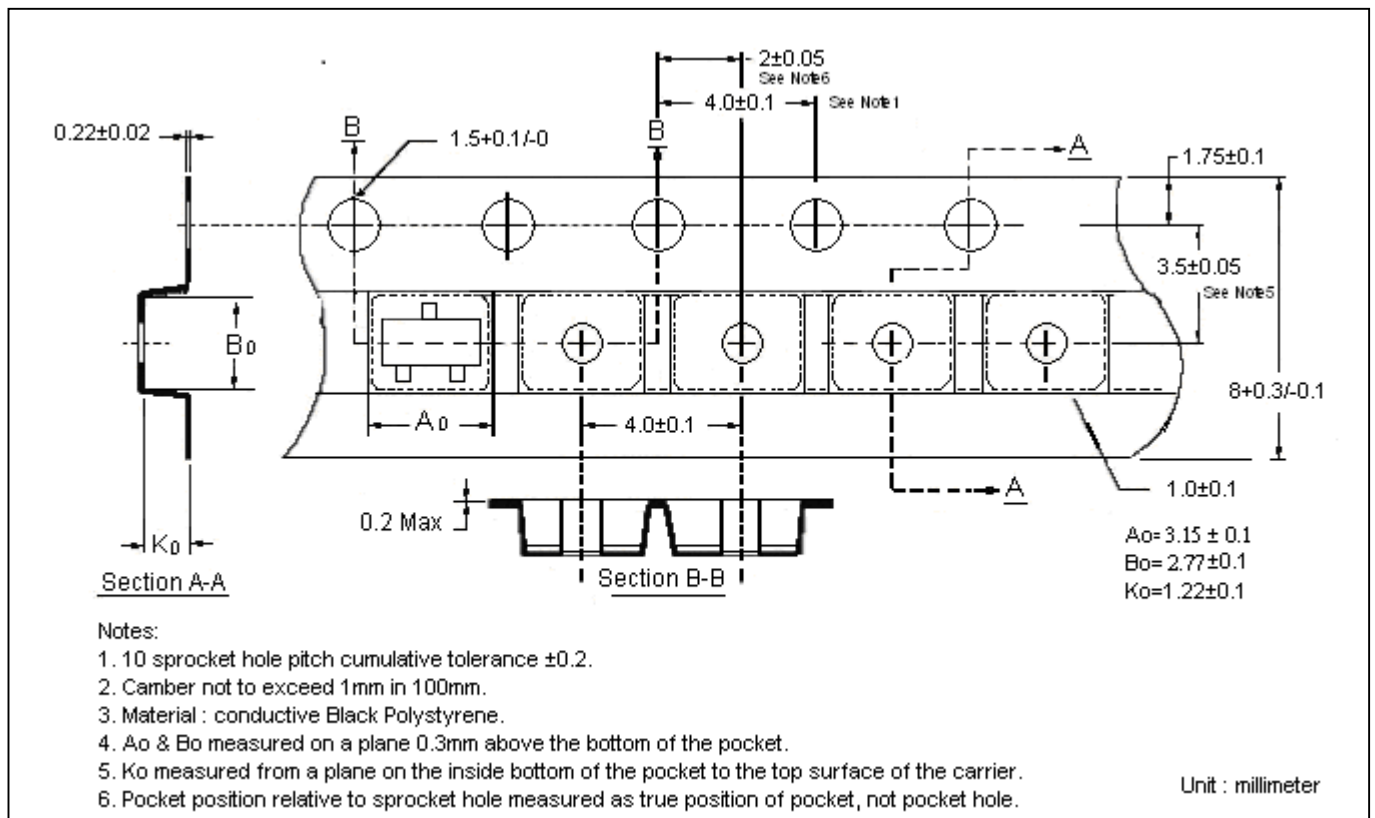
Recommended Soldering Footprint



Reel Dimension



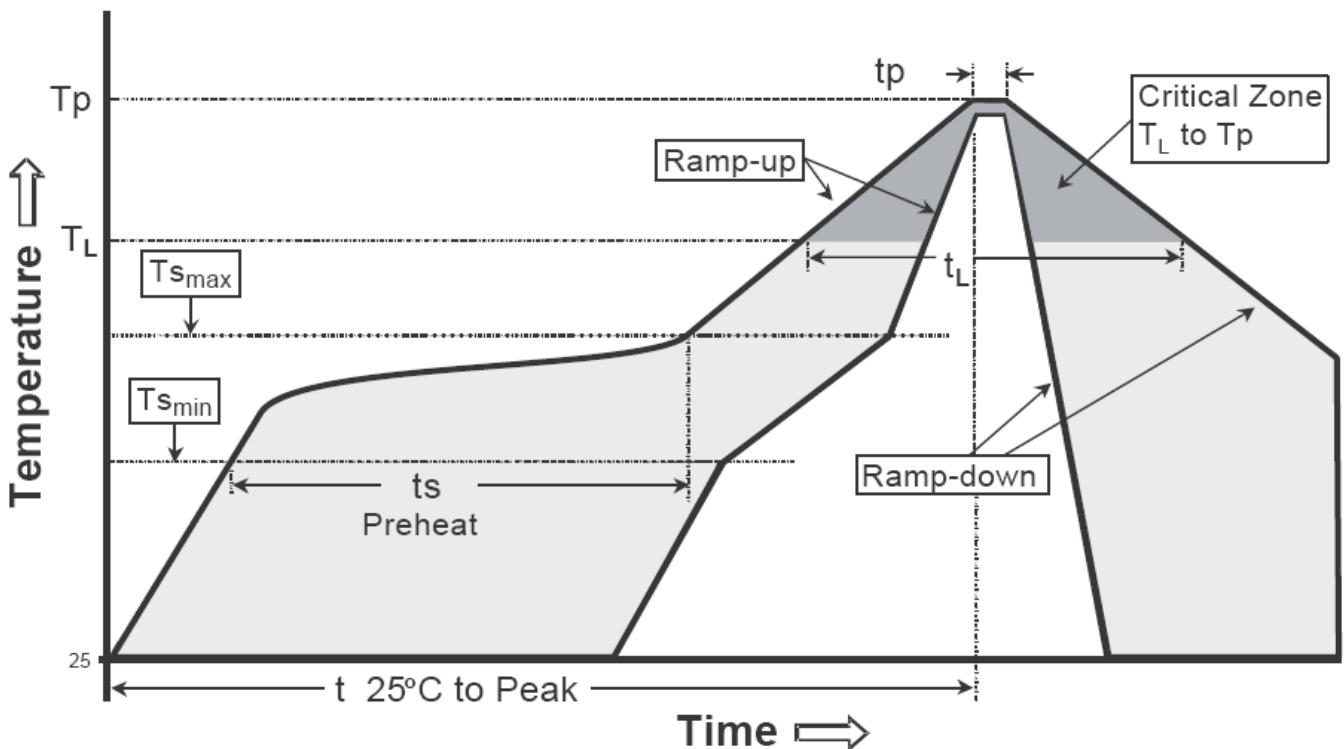
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

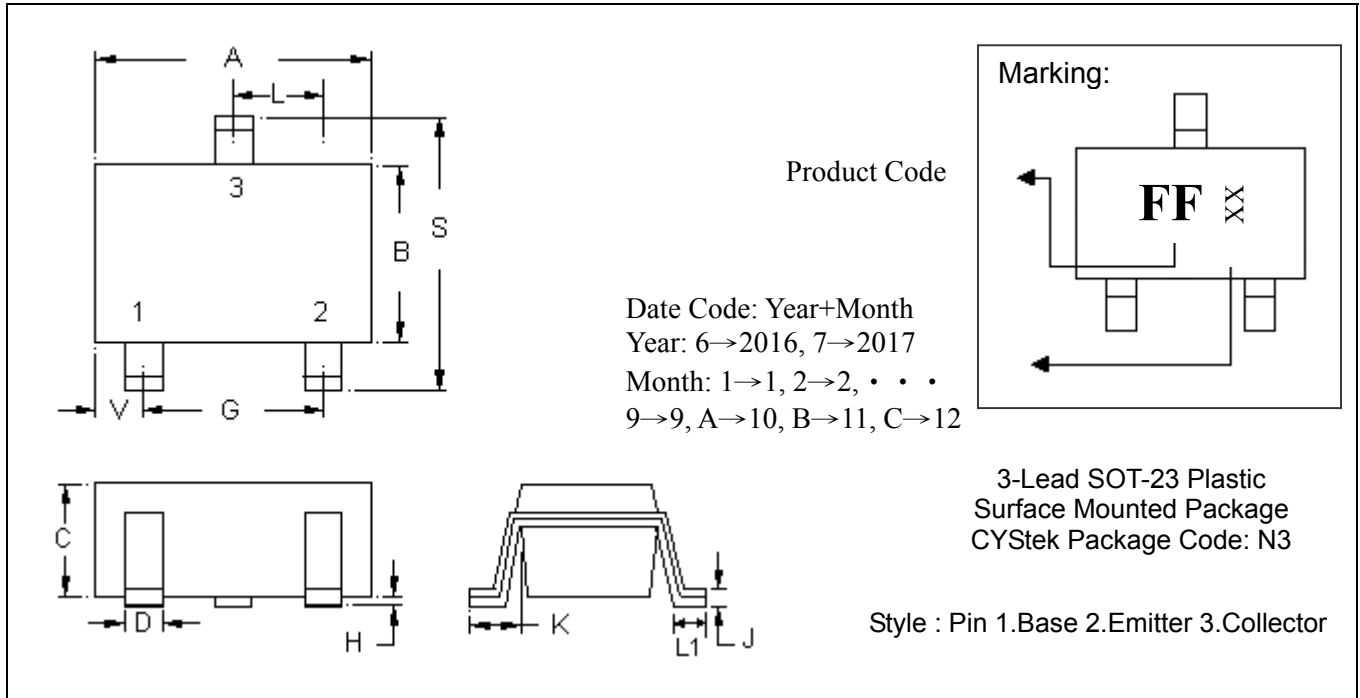
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0551	1.20	1.40	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1004	2.10	2.55
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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